

AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1. (Currently Amended): A semiconductor device fabrication method comprising:

a first polishing of polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry including abrasive grains and a surfactant is supplied onto [[the]] a polishing pad to planarize the surface of the film to be polished through a first nozzle; and

after the surface of the film to be polished has been planarized, further a second polishing of polishing the surface of the film-to-be-polished with a polishing pad while said polishing slurry is supplied onto a polishing pad through the first nozzle and water [[are]] is further supplied onto the polishing pad through a second nozzle different from the first nozzle, said polishing slurry and said water being supplied onto the polishing pad separately,

wherein said polishing slurry comprises abrasive grains and a surfactant additive, and

wherein in the further polishing the surface of the film to be polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle supply of said water through the second nozzle starts at the second polishing after the first polishing.

2 (Cancelled).

3. (Currently Amended): A semiconductor device fabrication method comprising:
according to claim 1, wherein

~~polishing a surface of a film to be polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to planarize the surface of the film to be polished; and~~

~~after the surface of the film to be polished has been planarized, further polishing the surface of the film to be polished with a polishing pad while said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately;~~

~~wherein said polishing slurry comprises abrasive grains and a surfactant additive;~~

~~wherein in the further second polishing the surface of the film to be polished, [[the]] said water is supplied to a position outer of a position for said polishing slurry to be supplied to, and~~

~~wherein in the further polishing the surface of the film to be polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle.~~

4. (Currently Amended): A semiconductor device fabrication method comprising:
according to claim 1, wherein

~~polishing a surface of a film to be polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to planarize the surface of the film to be polished; and~~

after the surface of the film to be polished has been planarized, further polishing the surface of the film to be polished with a polishing pad while said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately;

wherein said polishing slurry comprises abrasive grains and a surfactant additive;

wherein in the further second polishing the surface of the film to be polished, a supply amount of said water is 2 or more times as much as a supply amount of said polishing slurry; and

wherein in the further polishing the surface of the film to be polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle.

5-11 (Cancelled).

12. (Currently Amended): A semiconductor device fabrication method according to claim 1, further comprising, before the planarizing the surface of the film to be polished first polishing:

forming over [[the]] a semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,
in the ~~further second~~ polishing the surface of the film-to-be-polished, the surface of the
film-to-be-polished is polished with the insulation film as a stopper.

13-27 (Cancelled).

28. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

the abrasive grains comprise cerium oxide or silicon oxide,
the ~~additive surfactant~~ comprises poly(ammonium acrylate).

29-33 (Cancelled)

34. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

in the ~~further second~~ polishing the surface of the film-to-be-polished, a supply amount of said polishing slurry to a supply amount of said water is 1:5.

35. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

the polishing pad used in the further second polishing the surface of the film to be polished is different from the polishing pad used in the first polishing the surface of the film to be polished to planarize the surface of the film to be polished.

36 (Cancelled).